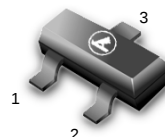


General Purpose Transistors

PNP Silicon

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

LMBT4403LT1



SOT- 23 (TO-236AB)

ORDERING INFORMATION

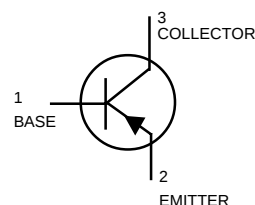
Device	Package	Shipping
LMBT4403LT1	SOT-23	3000/Tape & Reel
LMBT4403LT1G	SOT-23	3000/Tape & Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	- 40	Vdc
Collector-Base Voltage	V_{CBO}	- 40	Vdc
Emitter-Base Voltage	V_{EBO}	- 5.0	Vdc
Collector Current — Continuous	I_C	- 600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR -5 Board (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$



DEVICE MARKING

LMBT4403LT1 = 2T

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (3) ($I_C = -1.0\text{ mAdc}, I_B = 0$)	$V_{(BR)CEO}$	- 40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = -0.1\text{ mAdc}, I_E = 0$)	$V_{(BR)CBO}$	- 40	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = -0.1\text{ mAdc}, I_C = 0$)	$V_{(BR)EBO}$	- 5.0	—	Vdc
Base Cutoff Current ($V_{CE} = -35\text{ Vdc}, V_{EB} = -0.4\text{ Vdc}$)	I_{BEV}	—	- 0.1	μAdc
Collector Cutoff Current ($V_{CE} = -35\text{ Vdc}, V_{EB} = -0.4\text{ Vdc}$)	I_{CEX}	—	- 0.1	μAdc

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

3. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2.0\%$.

LMBT4403LT1

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS				
DC Current Gain (I _C = -0.1 mAdc, V _{CE} = -1.0 Vdc)	h _{FE}	30	—	—
(I _C = -1.0 mAdc, V _{CE} = -1.0 Vdc)		60	—	
(I _C = -10 mAdc, V _{CE} = -1.0 Vdc)		100	—	
(I _C = -150 mAdc, V _{CE} = -2.0 Vdc)(3)		100	300	
(I _C = -500 mAdc, V _{CE} = -2.0 Vdc)(3)		20	—	
Collector-Emitter Saturation Voltage(3) (I _C = -150mAdc, I _B = -15 mAdc)	V _{CE(sat)}	—	- 0.4	Vdc
(I _C = -500 mAdc, I _B = -50 mAdc)		—	- 0.75	
Base-Emitter Saturation Voltage (3) (I _C = -150 mAdc, I _B = -15 mAdc)	V _{BE(sat)}	- 0.75	- 0.95	Vdc
(I _C = -500 mAdc, I _B = -50 mAdc)		—	- 1.3	

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product (I _C = -20mAdc, V _{CE} = -10 Vdc, f = 100 MHz)	f _T	200	—	MHz
Collector-Base Capacitance (V _{CB} = -10 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	—	8.5	pF
Emitter-Base Capacitance (V _{BE} = -0.5 Vdc, I _C = 0, f = 1.0 MHz)	C _{eb}	—	30	pF
Input Impedance (V _{CE} = -10 Vdc, I _C = -1.0 mAdc, f = 1.0 kHz)	h _{ie}	1.5	15	kΩ
Voltage Feedback Ratio (V _{CE} = -10 Vdc, I _C = -1.0 mAdc, f = 1.0 kHz)	h _{re}	0.1	8.0	X 10 ⁻⁴
Small-Signal Current Gain (V _{CE} = -10 Vdc, I _C = -1.0 mAdc, f = 1.0 kHz)	h _{fe}	60	500	—
Output Admittance (V _{CE} = -10 Vdc, I _C = -1.0 mAdc, f = 1.0 kHz)	h _{oe}	1.0	100	μmhos

SWITCHING CHARACTERISTICS

Delay Time	(V _{CC} = -30 Vdc, V _{EB} = -2.0 Vdc,	t _d	—	15	ns
Rise Time	I _C = -150mAdc, I _{B1} = -15 mAdc)	t _d	—	20	
Storage Time	(V _{CC} = -30 Vdc, I _C = -150 mAdc,	t _s	—	225	ns
Fall Time	I _{B1} = I _{B2} = -15 mAdc)	t _f	—	30	

3. Pulse Test: Pulse Width ≤300 μs; Duty Cycle ≤2.0%.

SWITCHING TIME EQUIVALENT TEST CIRCUITS

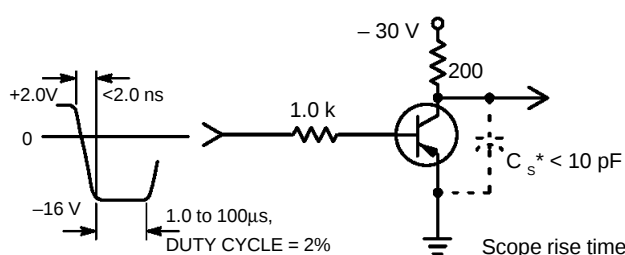


Figure 1. Turn-On Time

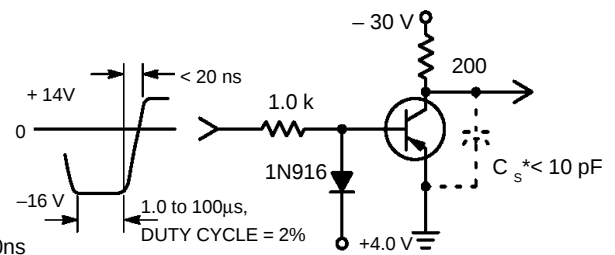
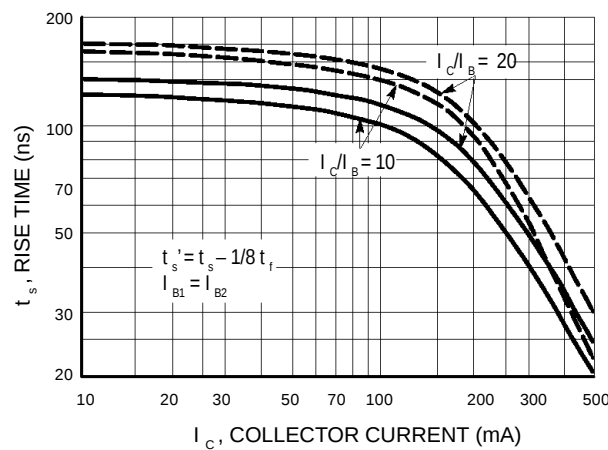
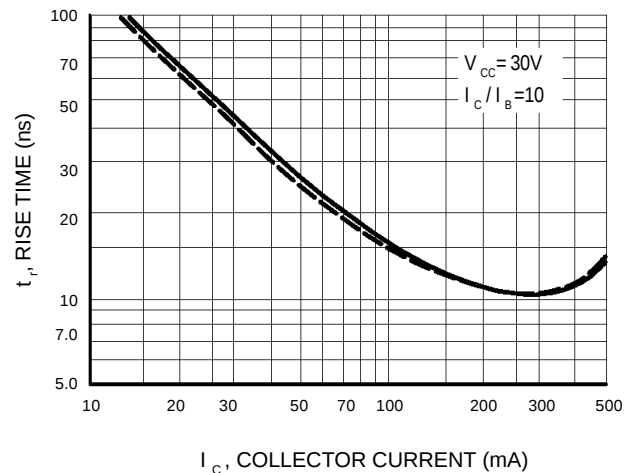
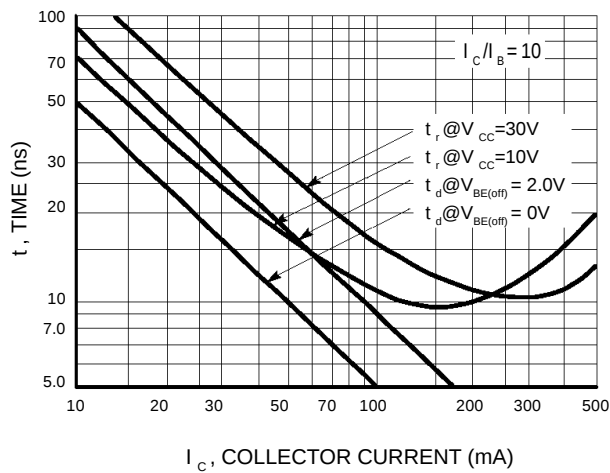
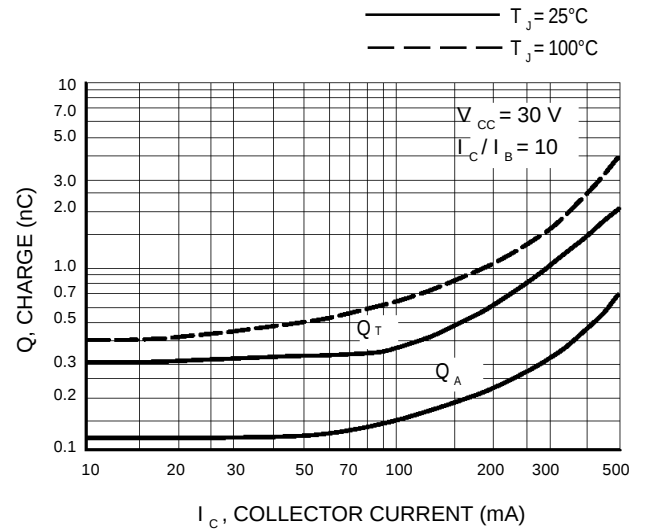
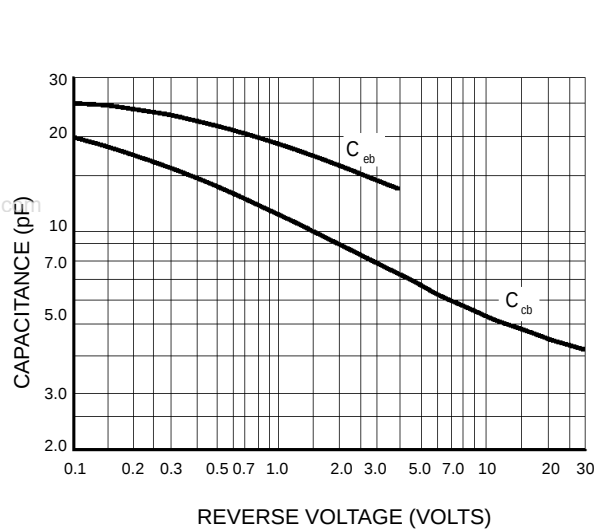


Figure 2. Turn-Off Time

*Total shunt capacitance of test jig connectors, and oscilloscope

LMBT4403LT1

TYPICAL TRANSIENT CHARACTERISTICS



LMBT4403LT1

SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE

$V_{CE} = -10 \text{ Vdc}$, $T_A = 25^\circ\text{C}$

Bandwidth = 1.0 Hz

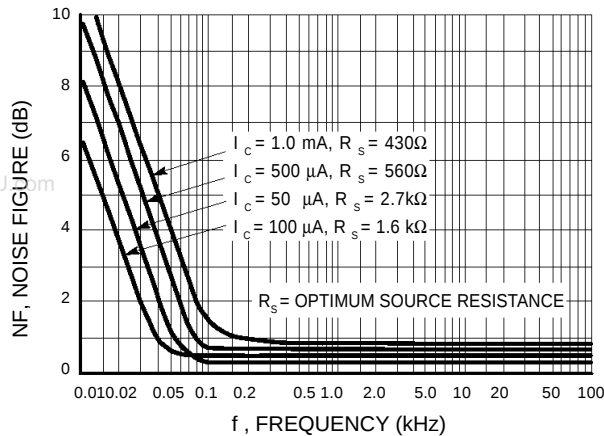


Figure 8. Frequency Effects

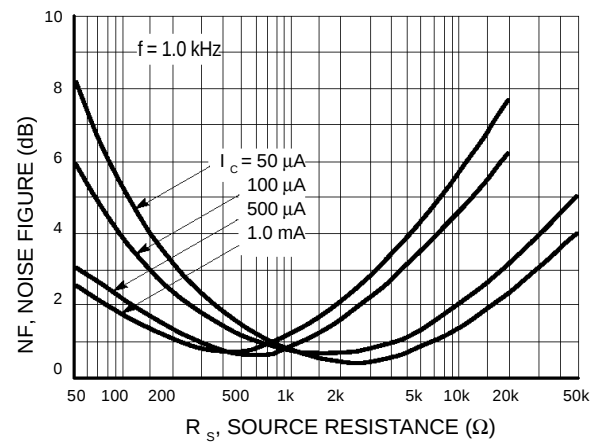


Figure 9. Source Resistance Effects

h PARAMETERS

($V_{CE} = -10 \text{ Vdc}$, $f = 1.0 \text{ kHz}$, $T_A = 25^\circ\text{C}$)

This group of graphs illustrates the relationship between h_{fe} and other "h" parameters for this series of transistors. To obtain these curves, a high-gain and a low-gain unit were selected from the MMBT4403LT1 lines, and the same units were used to develop the correspondingly numbered curves on each graph.

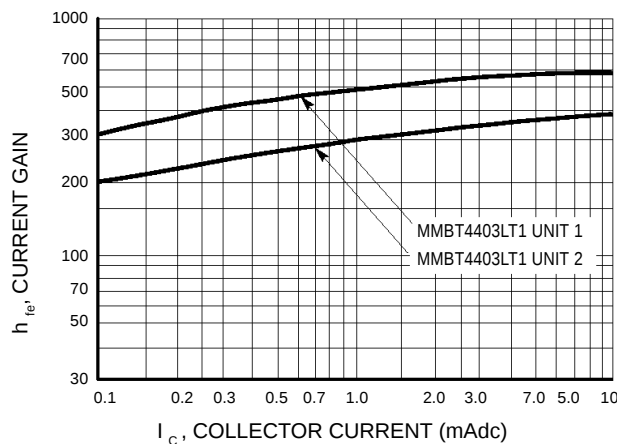


Figure 10. Current Gain

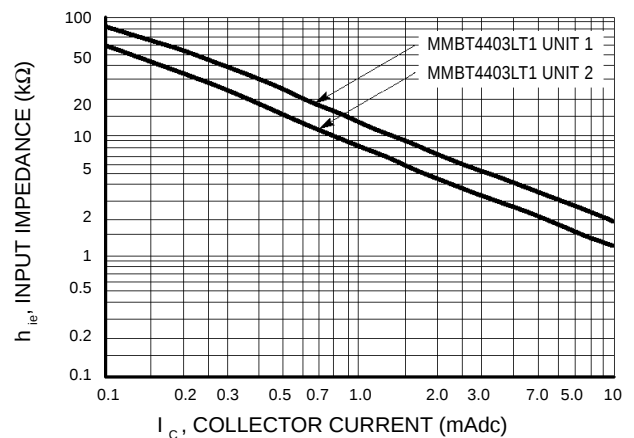


Figure 11. Input Impedance

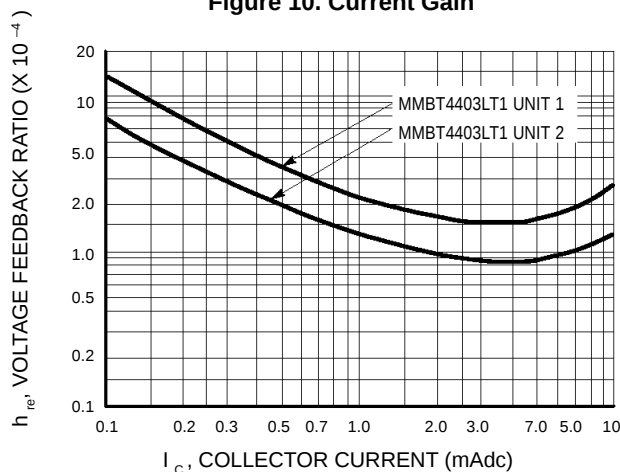


Figure 12. Voltage Feedback Ratio

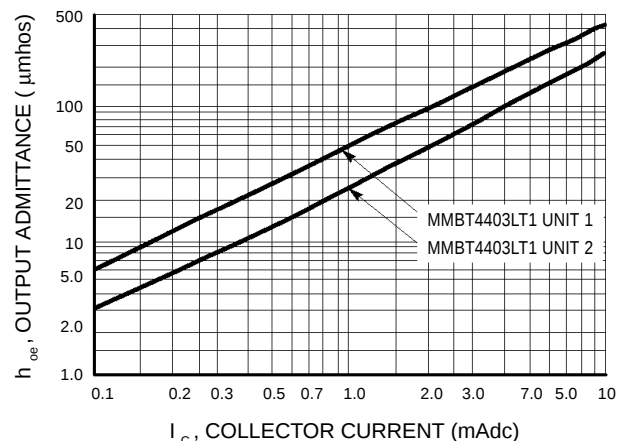


Figure 13. Output Admittance

LMBT4403LT1

STATIC CHARACTERISTICS

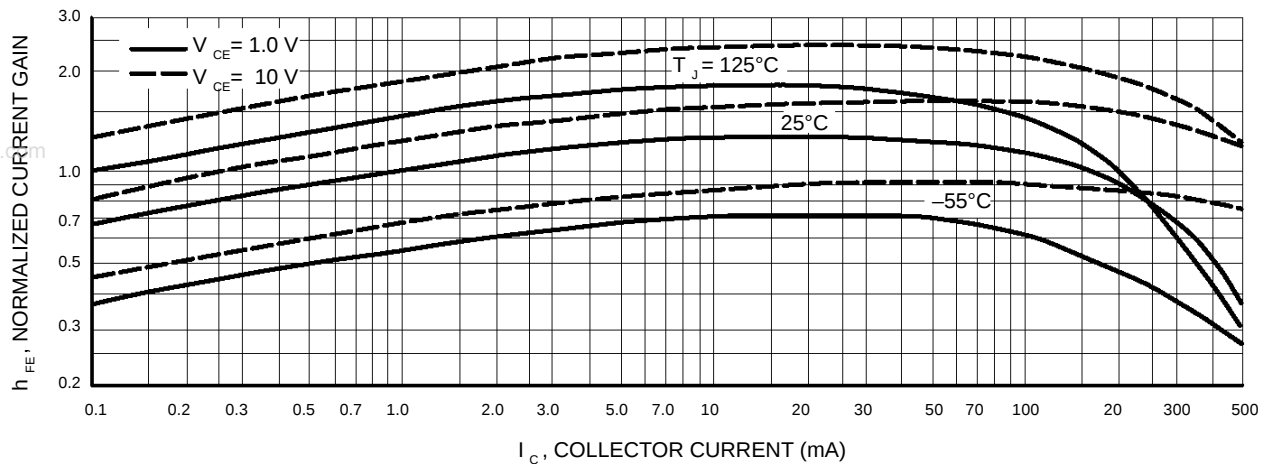


Figure 14. DC Current Gain

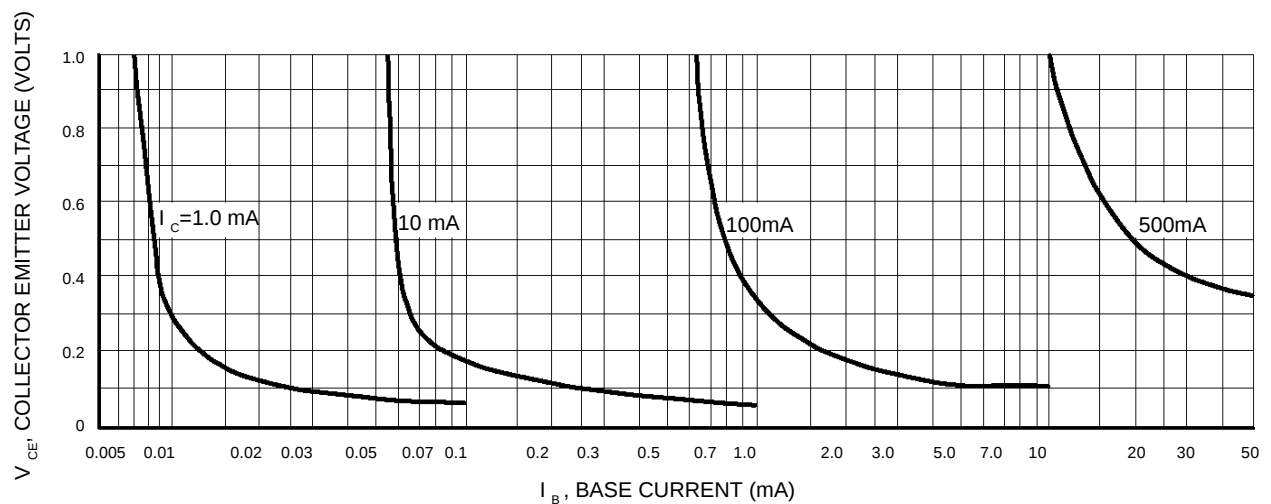


Figure 15. Collector Saturation Region

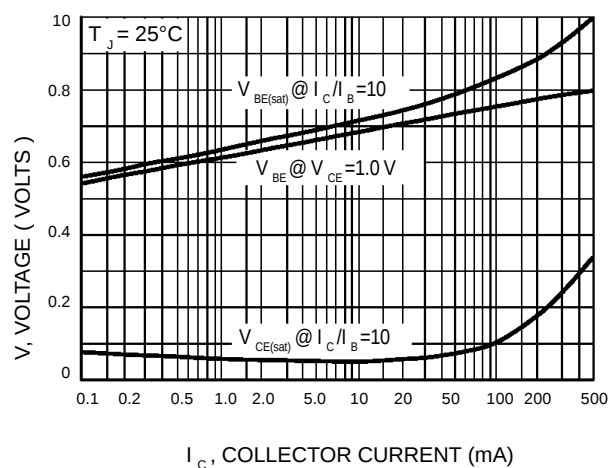


Figure 16. "On" Voltages

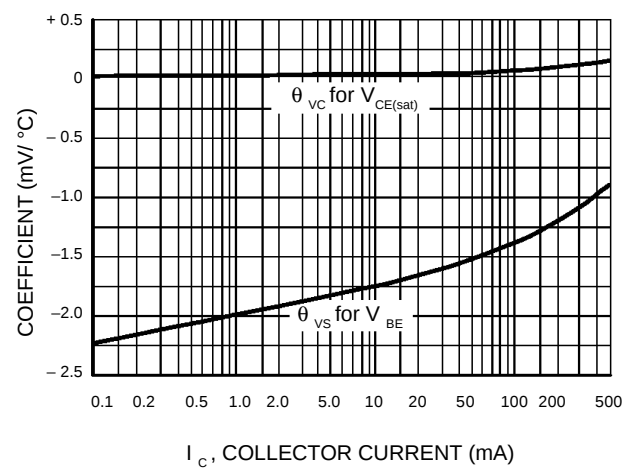


Figure 17. Temperature Coefficients